

MOS FET FKV660S

Absolute Maximum Ratings (Ta=25°C)

Symbol	Ratings	Unit
V _{DSS}	60	V
V _{GSS}	+20, -10	V
I _D	±60	A
I _{D(pulse)} **	±180	A
P _D	60(Tc=25°C)	W
T _{ch}	150	°C
T _{stg}	-40 to +150	°C

**P_w ≤ 100μs, duty ≤ 1%

Electrical Characteristics (Ta=25°C)

Symbol	Test Conditions	Ratings			Unit
		min	typ	max	
V(BR) _{DSS}	I _D =100μA, V _{GS} =0V	60			V
I _{GSS}	V _{GS} =+20V			+10	μA
	V _{GS} =-10V			-5	
I _{DSS}	V _{DS} =60V, V _{GS} =0V			100	μA
V _{TH}	V _{DS} =10V, I _D =250μA	1.0		2.5	V
R _e (yfs)	V _{DS} =10V, I _D =25A	20			S
R _{DS(ON)}	V _{GS} =10V, I _D =25A		11	14	mΩ
C _{iss}	V _{DS} =10V		2500		pF
C _{oss}	f=1.0MHz		900		pF
C _{rss}	V _{GS} =0V		150		pF
t _{d(on)}	I _D =25A		50		ns
t _r	V _{DD} ≈ 12V		400		ns
t _{d(off)}	R _L =0.48Ω, V _{GS} =10V		400		ns
t _f			300		ns
V _{SD}	I _{SD} =50A, V _{GS} =0V		1.0	1.5	V

External Dimensions T0220S

